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Pch -100V -1.5A Power MOSFET

V_{DSS}	-100V
R _{DS(on)} (Max.)	470m Ω
I _D	−1.5A
P_D	1.25W

RSQ015P10

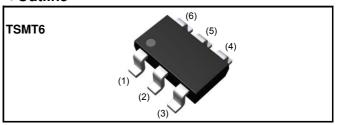
Features

- 1) Low on resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (TSMT6).
- 4) Pb-free lead plating; RoHS compliant

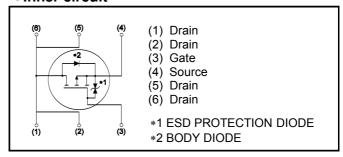
Application

DC/DC converters

Outline



•Inner circuit



Packaging specifications

	Packaging	Taping
	Reel size (mm)	180
Type	Tape width (mm)	8
Туре	Basic ordering unit (pcs)	3,000
	Taping code	TR
	Marking	ZN

● Absolute maximum ratings(T_a = 25°C)

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	-100	V
Continuous drain current	I _D *1	±1.5	Α
Pulsed drain current	I _{D,pulse} *2	±6.0	А
Gate - Source voltage	V_{GSS}	±20	V
Power dissipation	P _D *3	1.25	W
Power dissipation	P _D *4	0.6	W
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	−55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
- Farametei	Зуппоп	Min.	Тур.	Max.	Offic
Thermal resistance, junction - ambient	R _{thJA} *3	-	-	100	°C/W
Thermal resistance, junction - ambient	R _{thJA} *4	-	-	208	°C/W

•Electrical characteristics($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Parameter Symbol Conditions		Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -1 mA	-100	1	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_{j}}$	I _D = -1mA referenced to 25°C	-	-109	-	mV/°C
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -100V, V_{GS} = 0V$	-	1	-1	μΑ
Gate - Source leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±10	μΑ
Gate threshold voltage	V _{GS (th)}	$V_{DS} = -10V, I_{D} = -1mA$	-1.0	ı	-2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_{j}}$	I _D = -1mA referenced to 25°C	-	3.2	-	mV/°C
		V _{GS} = -10V, I _D = -1.5A	-	350	470	
Static drain - source	. *5	V_{GS} = -4.5V, I_{D} = -0.75A	-	380	510	 .
on - state resistance	$R_{DS(on)}$	V_{GS} = -4.0V, I_{D} = -0.75A	-	400	540	mΩ
		V _{GS} = -10V, I _D = -1.5A, T _j =125°C	-	610	850	
Gate input resistannce	R_{G}	f = 1MHz, open drain	-	8.5	1	Ω
Transconductance	g _{fs} *5	$V_{DS} = -10V, I_{D} = -1.5A$	1.5	4.0	-	S

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 $\mu s,~Duty~cycle \leq$ 1%

^{*3} Mounted on a ceramic board (30×30×0.8mm)

^{*4} Mounted on a FR4 (15×20×0.8mm)

^{*5} Pulsed

• Electrical characteristics ($T_a = 25$ °C)

Parameter	Symbol	Conditions	Values			Unit
- raiailletei	Syllibol	Conditions	Min.	Тур.	Max.	Offic
Input capacitance	C _{iss}	V _{GS} = 0V	-	950	-	
Output capacitance	C _{oss}	V _{DS} = -25V	-	45	-	pF
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	20	-	
Turn - on delay time	$t_{d(on)}^{*5}$	$V_{DD} \simeq -50V, V_{GS} = -10V$	-	10	-	
Rise time	t _r *5	$I_{D} = -0.75A$	-	15	-	no
Turn - off delay time	${\rm t_{d(off)}}^{*5}$	$R_L = 66\Omega$	-	60	-	ns
Fall time	t _f *5	$R_G = 10\Omega$	-	10	-	

•Gate Charge characteristics($T_a = 25$ °C)

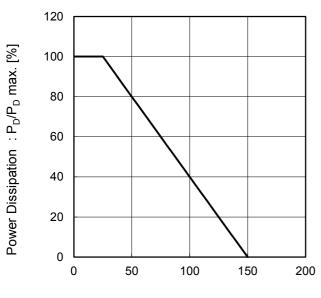
Parameter	Cumbal	Conditions	Values			Unit	
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic	
Total gate charge	. *5	${\sf Q_g}^{*5}$	$V_{DD} \simeq -50V, I_D = -1.5A$ $V_{GS} = -5V$	-	17.0	-	
Total gate charge	Q_g	$V_{DD} = -50V, I_D = -1.5A$ $V_{GS} = -10V$	-	32	-	nC	
Gate - Source charge	Q _{gs} *5	$V_{DD}^{\sim} -50V, I_{D} = -1.5A$ $V_{GS} = -5V$	-	4.5	-		
Gate - Drain charge	Q _{gd} *5	$V_{GS} = -5V$	-	5.0	-		

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai ii etei	Syllibol		Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _a = 25°C	-	-	-1.0	А
Forward voltage	V _{SD} *5	$V_{GS} = 0V, I_s = -1.5A$	-	ı	-1.2	V

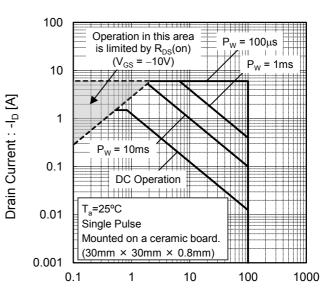
•Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

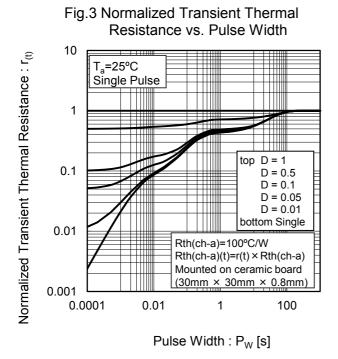


Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : -V_{DS} [V]



Peak Transient Power: P(W)

Fig.4 Single Pulse Maxmum

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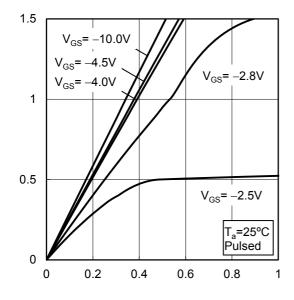
Pulse Width: Pw [s]

Drain Current: -I_D [A]

Drain - Source Breakdown Voltage : -V_{(BR)DSS} [V]

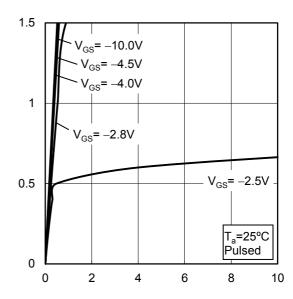
•Electrical characteristic curves

Fig.5 Typical Output Characteristics(I)



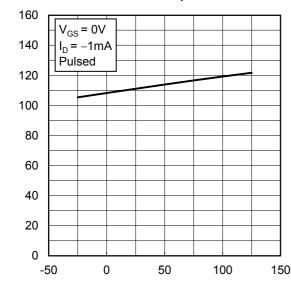
Drain - Source Voltage : -V_{DS} [V]

Fig.6 Typical Output Characteristics(II)



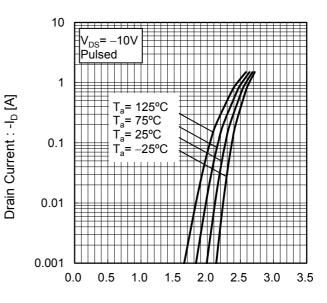
Drain - Source Voltage : -V_{DS} [V]

Fig.7 Breakdown Voltage vs. Junction Temperature



Junction Temperature : T_j [°C]

Fig.8 Typical Transfer Characteristics



Gate - Source Voltage : - V_{GS} [V]

Drain Current: -I_D [A]

Gate Threshold Voltage : - $V_{GS(th)}[V]$

•Electrical characteristic curves

Fig.9 Gate Threshold Voltage

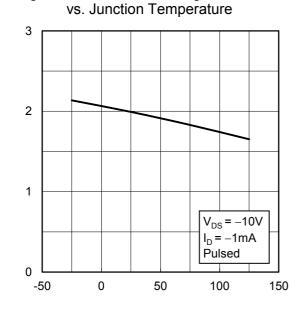
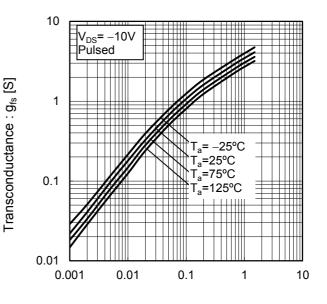


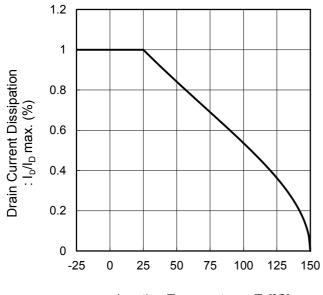
Fig.10 Transconductance vs. Drain Current



Junction Temperature : T_i [°C]

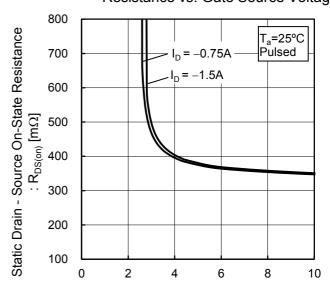
ture : T_j [°C] Drain Current : $-I_D$ [A]

Fig.11 Drain CurrentDerating Curve



Junction Temperature : T_i [°C]

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage



Gate - Source Voltage : -V_{GS} [V]

• Electrical characteristic curves

Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

1000

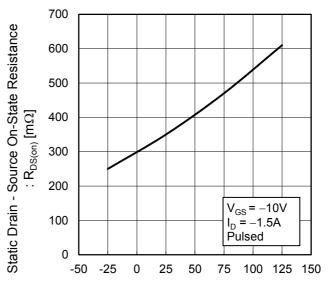
T_a=25°C

Pulsed

Static Drain - Source On-State Resistance On-S

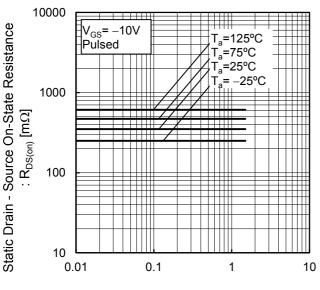
Drain Current: -ID [A]

Fig.14 Static Drain - Source On - State
Resistance vs. Junction Temperature



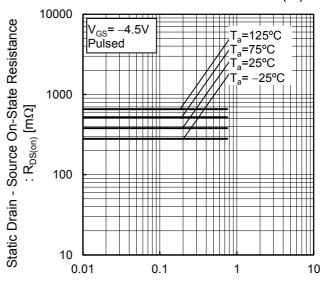
Junction Temperature : T_j [°C]

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(II)



Drain Current : -I_D [A]

Fig.16 Static Drain-Source On-State Resistance vs. Drain Current(III)



Drain Current : -I_D [A]

•Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(IV)

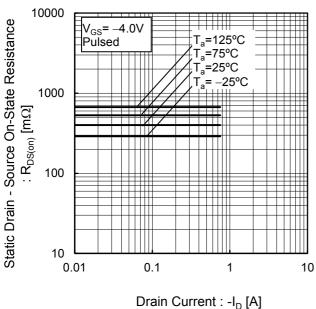
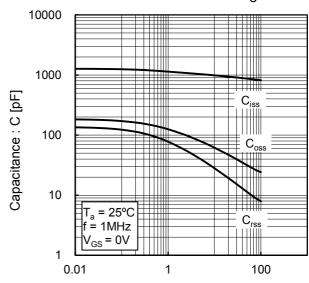


Fig.18 Typical Capacitance vs. Drain - Source Voltage



Drain - Source Voltage : -V_{DS} [V]

Fig.19 Switching Characteristics

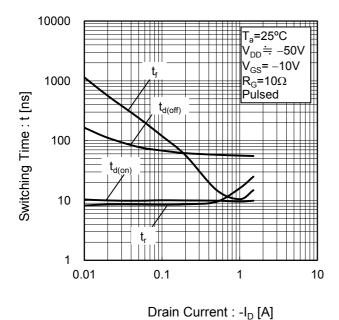
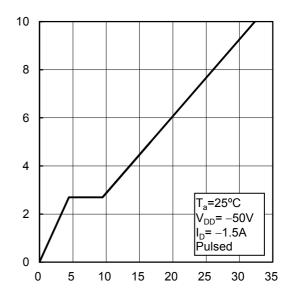


Fig.20 Dynamic Input Characteristics

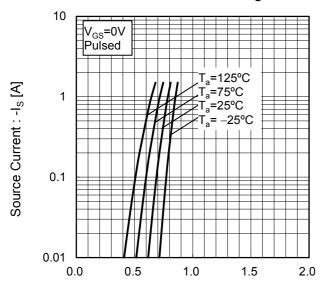


Total Gate Charge : Qq [nC]

Gate - Source Voltage : - $\mathsf{V}_{\mathsf{GS}}\left[\mathsf{V}\right]$

•Electrical characteristic curves

Fig.21 Source Current vs. Source Drain Voltage



Source-Drain Voltage : - V_{SD} [V]

● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

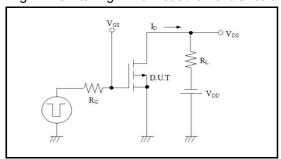


Fig.2-1 Gate Charge Measurement Circuit

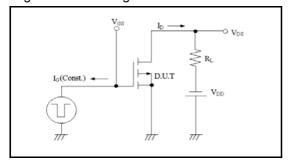


Fig.1-2 Switching Waveforms

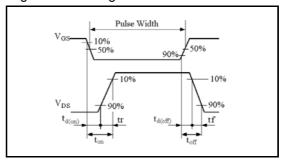
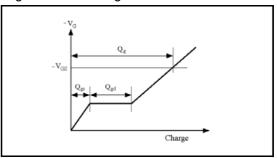
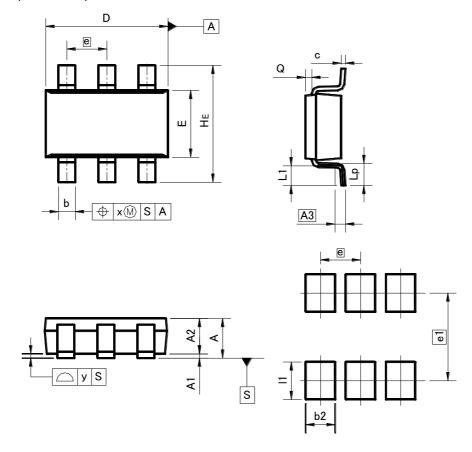


Fig.2-2 Gate Charge Waveform



●Dimensions (Unit: mm)





Patterm of terminal position areas

DIM	MILIMI	ETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	ı	1.00	ı	0.039
A1	0.00	0.10	0	0.004
A2	0.75	0.95	0.03	0.037
A3	0.2	25	0.0	01
b	0.35	0.50	0.014	0.02
С	0.10	0.26	0.004	0.01
D	2.80	3.00	0.11	0.118
Е	1.50	1.80	0.059	0.071
е	0.9	95	0.0	04
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.01
х	-	0.20	_	0.008
У	_	0.10	_	0.004

DIM MILIMETERS		INC	HES	
MIN		MAX	MIN	MAX
e1	2.	10	0.08	
b2		0.70	-	0.028
l1	-	0.90	ı	0.035

Dimension in mm/inches

Notes

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